

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
21 April 2005 (21.04.2005)

PCT

(10) International Publication Number
WO 2005/036653 A1

(51) International Patent Classification⁷: **H01L 29/786**,
G02F 1/1368, G09F 9/35, G09G 3/18, H01L 27/088

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(21) International Application Number:
PCT/KR2004/002611

(81) Designated States (*unless otherwise indicated, for every kind of national protection available*): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date: 13 October 2004 (13.10.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
10-2003-0071090 13 October 2003 (13.10.2003) KR

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(84) Designated States (*unless otherwise indicated, for every kind of regional protection available*): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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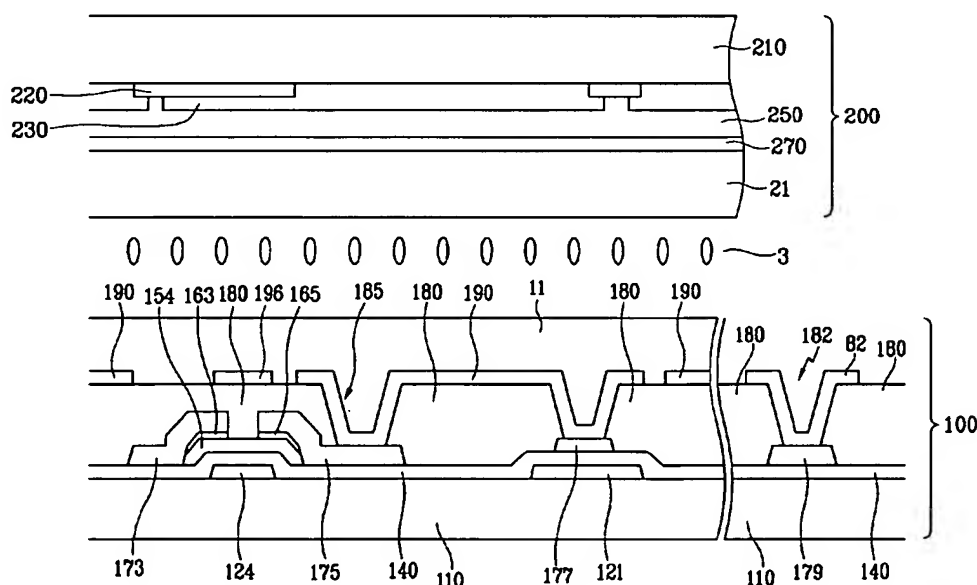
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Published:

— with international search report

[Continued on next page]

(54) Title: THIN FILM TRANSISTOR, THIN FILM TRANSISTOR ARRAY PANEL, AND DISPLAY DEVICE



(57) Abstract: A thin film transistor is provided, which includes: a gate electrode (124); a gate insulating layer (140) formed on the gate electrode; a semiconductor layer (154) formed on the gate insulating layer and disposed opposite the gate electrode; a source electrode (173) and a drain electrode (175) that are formed at least in part on the semiconductor layer and face each other; a passivation layer (180) formed on the source electrode, the drain electrode, and a portion of the semiconductor layer that is not covered with the source electrode and the drain electrode; and a shielding electrode (196) formed on the passivation layer and disposed on a region between the source electrode and the drain electrode.

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